

L Number	Hits	Search Text	DB	Time stamp
-	570	257/536	USPAT	2003/06/03 14:36
-	294	257/537	USPAT	2004/08/30 16:13
-	215	257/536 and (resistor film) and (heat conductor)	USPAT	2002/07/02 13:55
-	111	257/537 and (resistor film) and (heat conductor)	USPAT	2002/01/24 17:17
-	72	heat and (conductor adj film) and (resistor adj film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 16:15
-	320	257/536 and (resistor film) and (heat conductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/03 09:20
-	12	257/536 and (heat same resistor same conductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/03 09:34
-	12	257/537 and ( thickness same resistor same conductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/05 08:50
-	12	438/238 and ( thickness same resistor same conductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/03 11:28
-	63	438/381 and thickness and resistor and conductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/03 14:53
-	72	438/381 and resistor and conductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/08 07:54
-	226	257/\$.ccls. and resistor and (heat adj conduct\$3) and substrate and (wiring or terminal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 16:36
-	1382	257/536	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/30 15:50
-	1321	257/536 and resist\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/30 16:06
-	42	257/536 and resist\$5 and wiring and substrate and (silicon adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/12 11:01
-	22	257/536 and resist\$5 and (heat near conduct\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/30 16:29

-	21	257/536 and resist\$4 and (heat adj conduct\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/12 10:58
-	19	257/537 and resist\$5 and wiring and substrate and (silicon adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/12 11:11
-	46	257/536 and resist\$5 and wiring and substrate and (silicon adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/12 11:11
-	39	257/538 and resist\$5 and wiring and substrate and (silicon adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/12 11:32
-	779	257/536	USPAT	2004/08/30 16:21
-	367	257/537	USPAT	2004/08/30 16:24
-	398	257/538	USPAT	2004/08/30 16:28
-	290	257/539	USPAT	2004/08/30 16:31
-	38	257/540	USPAT	2004/08/30 16:32
-	73	257/541	USPAT	2004/08/30 16:33
-	67	257/542	USPAT	2004/08/30 16:34
-	80	257/543	USPAT	2004/08/30 16:36
-	468	257/358	USPAT	2004/08/30 16:40
-	290	257/359	USPAT	2004/08/30 16:43
-	233	257/154	USPAT	2004/08/30 16:46
-	391	257/363	USPAT	2004/08/30 16:50
-	911	257/379	USPAT	2004/08/30 16:58
-	408	257/380	USPAT	2004/08/30 17:02
-	414	438/382	USPAT	2004/08/30 17:07
-	580	438/309	USPAT	2004/08/30 17:07